

ABSTRACT

b1 The present invention provides a ceramic substrate which can keep a sufficiently large breakdown voltage even if the pore diameter of its maximum pore is 50 μm or less to be larger than that of conventional ceramic substrates, can give a large fracture toughness value because of the presence of pores, can resist thermal impact, and can give a small warp amount at high temperature. The ceramic substrate of the present invention is a ceramic substrate for a semiconductor-producing/examining device having a conductor formed on a surface of the ceramic substrate or inside the ceramic substrate, wherein: the substrate is made of a non-oxide ceramic containing oxygen; and the pore diameter of the maximum pore thereof is 50 μm or less.